THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-Case	Max	2.27	°C/W
R _{thj-amb}	Thermal Resistance Junction-Ambient	Max	80	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

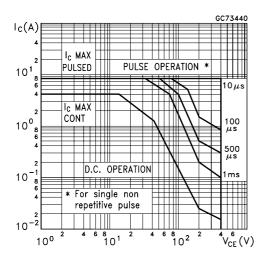
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
ICES	Collector Cut-off Current (V _{BE} = -1.5 V)	V _{CE} = 700 V V _{CE} = 700 V	T _C = 125 °C			100 500	μΑ μΑ
I _{CEO}	Collector-Emitter Leakage Current (I _B = 0)	V _{CE} = 400 V				250	μA
BV _{EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 10 mA		9		18	0 V
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	L = 25 mH	400	00,		V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 0.5 A I _C = 1 A I _C = 2.5 A	$I_{B} = 0.1 A$ $I_{B} = 0.2 A$ $I_{B} = 0.5 A$			0.7 1 1.5	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	$I_{C} = 0.5 A$ $I_{C} = 1 A$ $I_{C} = 2.5 A$	$I_B = 0.1 A$ $I_B = 0.2 A$ $I_B = 0.5 A$			1.1 1.2 1.3	V V V
h _{FE} *	DC Current Gain	I _C = 10 mA I _C = 2 A	V _{CE} = 5 V V _{CE} = 5 V	10 8		40	
Vf	Forward Voltage Drop	$I_f = 2 A$				2.5	V
t _s t _f	RESISTIVE LOAD Storage Time Fall Time	V _{CC} = 250 V I _{B1} = 0.4 A T _p = 30 μs	$I_{C} = 2 A$ $I_{B2} = -0.4 A$ (see fig. 2)	2	0.2	2.9	μs μs
ts tf	INDUCTIVE LOAD Storage Time Fall Time	$V_{CC} = 200 V I_{B1} = 0.4 A R_{BB} = 0 \Omega (see fig. 1)$	$I_{C} = 2 A$ $V_{BE(off)} = -5 V$ $L = 200 \mu H$		0.6 0.1		μs μs

57

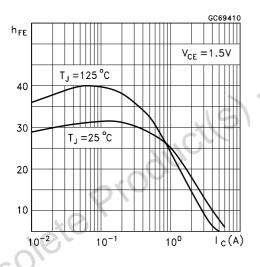
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

2/7

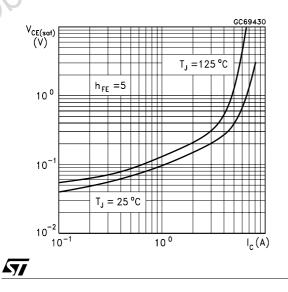
Safe Operating Areas

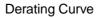


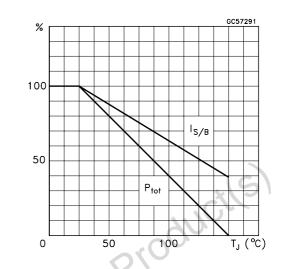
DC Current Gain

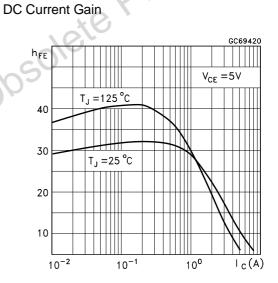


Collector Emitter Saturation Voltage

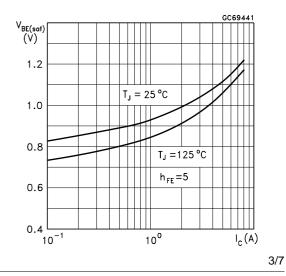




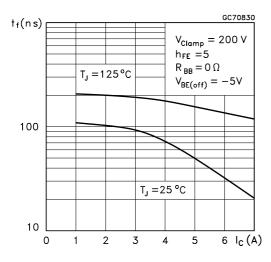




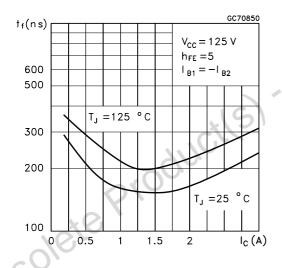




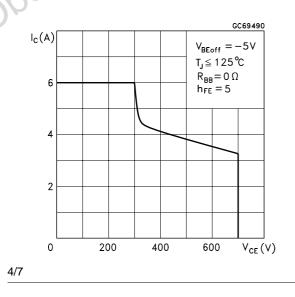
Inductive Fall Time



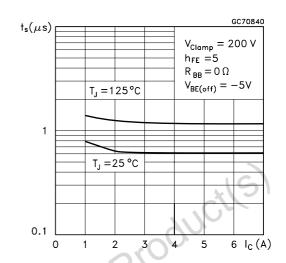
Resistive Load Fall Time

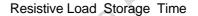


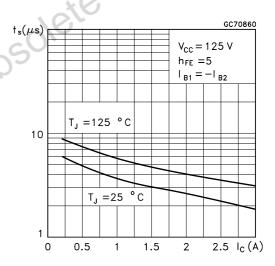
Reverse Biased SOA



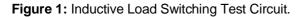
Inductive Storage Time







57



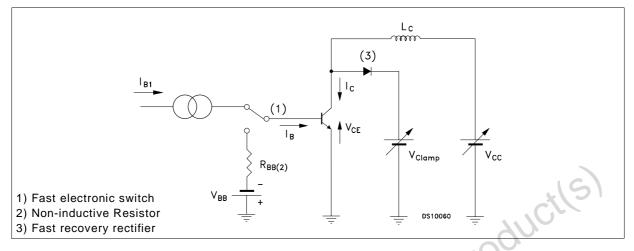
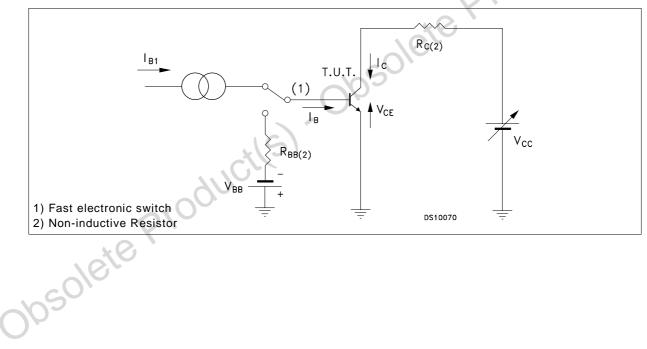


Figure 2: Resistive Load Switching Test Circuit.

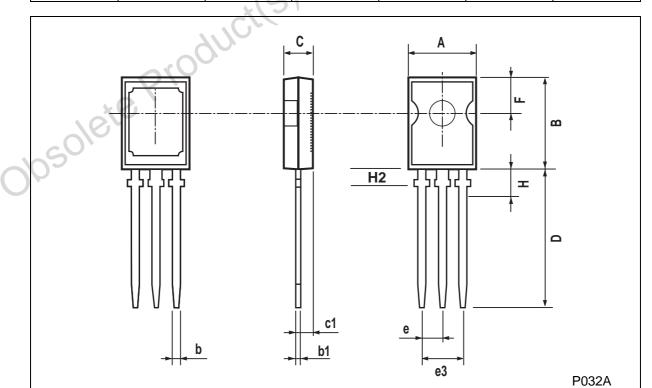




BULK128D-B

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.444
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.04		0.106
c1	1.0		1.3	0.039	du	0.05
D	15.4		16	0.606	26	0.629
е		2.2		×0	0.087	
e3	4.15		4.65	0.163		0.183
F		3.8		5	0.150	
Н			2.54		0.100	
H2		2.15			0.084	

SOT-82 MECHANICAL DATA



57

obsolete Product(s)- Obsolete Product(s)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

